

ABSTRACT OF THE DISCLOSURE

An active matrix type organic light emitting diode device and a thin film transistor thereof are disclosed in the present invention. The driving thin film transistor for an active matrix type organic light emitting diode (AMOLED) device having first and second electrodes spaced apart from each other and an organic light emitting layer disposed between the first and second electrodes includes a gate electrode on a substrate, a semiconductor layer over the gate electrode, and source and drain electrodes on the semiconductor layer, wherein the source and drain electrodes are spaced apart from each other and respectively overlap portions of the gate electrode, and an overlapping area between the gate electrode and the source electrode is larger than an overlapping area between the gate electrode and the drain electrode.